2SC3149

**Preliminary** 

# NPN SILICON TRANSISTOR

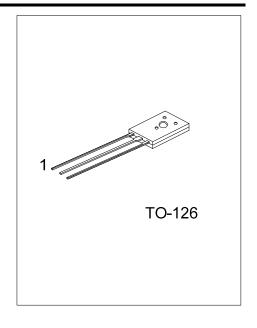
# **NPN TRANSISTOR**

## **DESCRIPTION**

The UTC 2SC3149 are series of NPN silicon planar transistor, and its suited to be used in power amplifier applications.

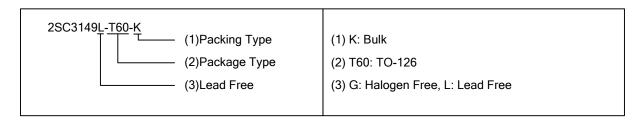
#### **FEATURES**

\* Suit for power amplifier applications



#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Dooking	
Lead Free	Halogen Free	Fackage	1	2	3	Packing	
2SC3149L-T60-K	2SC3149G-T60-K	TO-126	В	С	Е	Bulk	



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## ■ ABSOLUTE MAXIMUM RATING

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	1200	V
Collector-emitter voltage	V <sub>CEO</sub>	800	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Collector Current	Ic	0.5	А
Collector Dissipation	Pc	2	W
Junction Temperature	TJ	+150	$^{\circ}\mathbb{C}$
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =1mA, I <sub>E</sub> =0A	1200			V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =5mA, I <sub>B</sub> =0A	800			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	I <sub>E</sub> =1mA, I <sub>C</sub> =0A	7			V
Collector Cutoff Current	I <sub>CBO</sub>	$V_{CB}$ =800V, $I_{E}$ =0A			10	μΑ
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0A			10	μΑ
DC Current Gain (Note)	$h_{FE}$	I <sub>C</sub> =100mA, V <sub>CE</sub> =5V	10		40	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I <sub>C</sub> =200mA, I <sub>B</sub> =40mA			0.8	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I <sub>C</sub> =200mA, I <sub>B</sub> =40mA			1.5	V
Current Gain Bandwidth Product	f⊤	I <sub>C</sub> =100mA, V <sub>CE</sub> =10V		15		MHz
Output Capacitance	Сов	V <sub>CB</sub> =10V, f=1MHz		30		pF
Turn-On Time	ton				1.0	μs
Storage Time	t <sub>STG</sub>	I <sub>C</sub> =1A, I <sub>B1</sub> =0.2A, I <sub>B2</sub> =-0.4A, R <sub>I</sub> =400Ω, V <sub>CC</sub> =400V			3.0	μs
Fall Time	t <sub>F</sub>	11(_400\$2, VCC_400V			0.7	μs

Note: Pulse test: Pulse width=300µs, Duty Cycle ≤ 2%

## ■ CLASSIFICATION OF h<sub>FE</sub>

RANK	K	L	M
RANGE	10 ~ 20	15 ~ 30	20 ~ 40

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